

V1.1 Datasheet

P-Channel -40V MOSFET

FEATURES

- ●Trench Process Technology
- ●Ultra Low On-resistance Design

Application

- ●BMS Application
- ●Consumer Electronics
- ●DC/DC Converters

Mechanical

●Case:DFN5060 Package

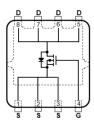
Packing Information

Package	Packing
DFN5060	3K/13" Reel

PRODUCTY SUMMARY					
V _{DS}	$R_{DS(on)}(m\Omega)$ Max				
-40	13	@V _{GS} =-10V			
-40	20	@V _{GS} =-4.5V			

DFN5060





Maximum Ratings (T _A =25°C unless otherwise specified)							
Parameter	Symbol	Limit	Unit				
Drain-Source Voltage	V _{DS}	-40	V				
Gate-Source Voltage	V _{GS}	±20	V				
Continuous Drain Current 1)	I _{DSM}	-20	А				
Continuous Drain Current 4)	I _D	-80	А				
Continuous Drain Current 5)	I _{DM}	-228	А				
Maximum Power Dissipation	P _D	6	W				
Operating Junction and Storage Temperature Range	T _J , T _{STG}	-55 to 150	°C				

Typical Thermal Resistance						
Parameter Symbol Limit Unit						
Junction-to-Ambient Thermal Resistance 5)	$R_{\theta JA}$	65	°C/W			

Note:

- 1. Pulse width<300us, Duty cycle<2%.
- 2. Fused current that based on wire numbers and diameter.
- 3. Guaranteed by design, not subject to production testing.
- 4. The maximum current rating is package limited.
- 5. Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)}$ =150°C. Ratings are based on low frequency and duty cycles to keep initial T_J =25°C.

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Electrical Characteristics (T _A = 25°C UNLESS OTHERWISE NOTED)						
Characteristics	Symbol	Test Condition	Limits			l lmit
			Min	Тур	Max	Unit
Static						
Drain-Source Breakdown Voltage	B _{VDSS}	V_{GS} =0V, I_D =-250 μ A	-40	1	-	V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$, $I_{D}=-250\mu A$	-1.0	-1.6	-2.5	V
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} =-10.0V, I _D =-10A	-	11.5	13	mΩ
Dialit-Source Off-State Resistance		V_{GS} =-4.5V, I_D =-8A	-	16.5	20	mΩ
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-40V, V _{GS} =0V	-	-	-1.0	μΑ
GateSource Leakage Current	I _{GSS}	V_{GS} =±20V, V_{DS} =0V	-	-	-100	nA

Dynamic ³⁾						
Total Gate Charge	Q_g	.,	-	24	-	
Gate-Source Charge	Q_{gs}	V_{DS} =-20V, V_{GS} =0 to - 4.5V, I_{D} =-1.5A	-	3	-	nC
Gate-Drain Charge	Q_{gd}	, ,	-	13	-	
Input Capacitance	C _{iss}		-	2675	-	
Output Capacitance	C _{oss}	V _{DS} =-20V, V _{GS} =0V, f=200kHz	-	216	-	pF
Reverse Transfer Capacitance	C _{rss}		-	199	-	

Switching						
Turn-On Delay Time	t _{d(on)}		-	19	-	
Turn-On Rise Time	t _r	V _{DS} =-20V, V _{GS} =-10V,	-	16	-	nc
Turn-Off Delay Time	t _{d(off)}	Rg=3.0Ω	-	61	-	ns
Turn-Off Fall Time	t _f		-	14	-	

Drain-Source Diode						
Maximum Continuous Body Diode Forward Current	I _S	T _C =25°C	-	-	-1.2	А
Diode Forward Voltage	V_{SD}	I _S =-1.0A, V _{GS} =0V	-	-	-1.5	V

Note:

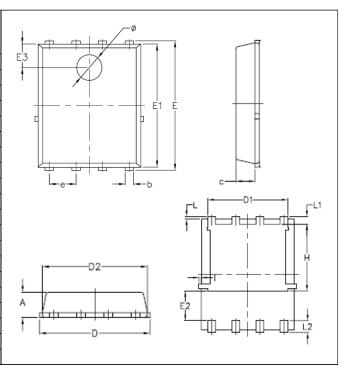
- 1. Pulse width<300us, Duty cycle<2%.
- 2. Essentially independent of operating temperature typical characteristics.
- 3. Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)}$ =150°C. Ratings are based on low frequency and duty cycles to keep initial T_J =25°C.
- 4. The maximum current rating is package limited.
- 5. R_{0,JA} is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch2 with 2oz.square pad of copper.
- 6. Guaranteed by design, not subject to production testing.

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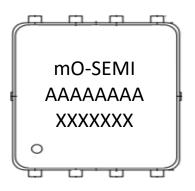


Package Outline Dimensions (inches and millimeters)

DFN5060						
		Dime	nsions			
SYMBOL	Millim	Millimeters Inc		hes		
	Min	Max	Min	Max		
Α	1.03	1.17	0.041	0.046		
b	0.34	0.48	0.013	0.019		
С	0.82	0.97	0.032	0.038		
D	4.80	5.40	0.189	0.213		
D1	4.11	4.31	0.162	0.170		
D2	4.80	5.00	0.189	0.197		
Е	5.95	6.15	0.234	0.242		
E1	5.65	5.85	0.222	0.230		
E2	1.40	-	0.055	-		
E3	1.00	1.20	0.039	0.047		
е	1.27	1.27 BSC		BSC		
L	0.05	0.25	0.002	0.010		
L1	0.38	0.50	0.015	0.020		
L2	0.38	0.71	0.015	0.028		
Н	3.30	3.50	0.130	0.138		
- 1	•	0.18	-	0.007		
Ф	1.10	1.30	0.043	0.051		



Marking Information



First line = Company name

AAAAAAA = Product number

XXXXXXX = Tracking number

Fourth line = Pin1 Point

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